



TO-252 Plastic-Encapsulated Transistors

2SD1899-Z TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 2 W ($T_{amb}=25^{\circ}C$)

Collector current

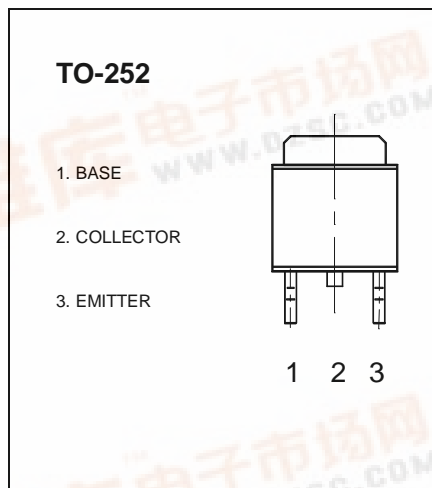
I_{CM} : 3 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specific)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=200mA$	60			
	$h_{FE(2)}$	$V_{CE}=2V, I_C=600mA$	100		400	
	$h_{FE(3)}$	$V_{CE}=2V, I_C=2A$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1.5A, I_B=150mA$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1.5A, I_B=150mA$			1.2	V
Transition frequency	f_T	$V_{CE}=5V, I_C=1.5A$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		30		pF
Switching Time	Turn on Time	t_{on}		0.5		μs
	Storage Time	t_{stg}	$V_{CC}=30V, I_C=1A, I_{B1}=-I_{B2}=-0.05A$	2.0		
	Fall Time	t_f		0.5		

CLASSIFICATION OF $h_{FE(1)}$

Rank	M	L	K
Range	100-200	160-320	200-400

